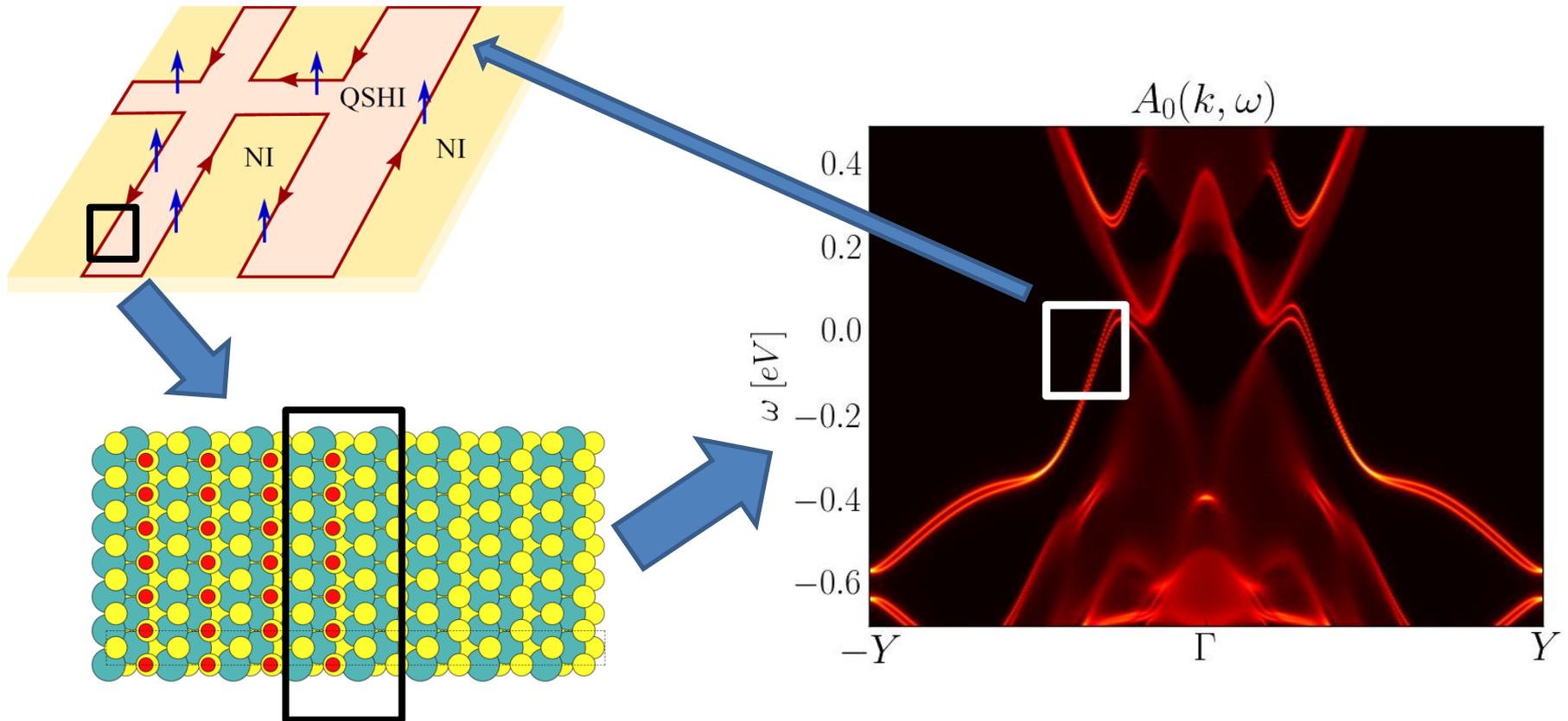


Designing topological in-plane heterostructures from first principles: 1T'-MoS₂



Outline

- Spin-orbit coupling in GPAW
- Two-dimensional topological insulators
- Topological in-plane heterostructure with 1T'-MoS₂
- Metallic boundary states

The Dirac equation is

$$[\beta mc^2 + c\boldsymbol{\alpha} \cdot \mathbf{p} + V(x)]\psi(x) = E\psi(x)$$

where $\boldsymbol{\alpha}$ and β are 4x4 matrices, which can be written in terms of the Pauli matrices.

Writing

$$\psi(x) = \begin{bmatrix} \xi(x) \\ \eta(x) \end{bmatrix}$$

eliminating η and expanding to second order in $(E - V)/mc^2$ yields

$$\left[\frac{p^2}{2m} + V(x) - \frac{p^4}{8m^3c^2} - \frac{i\hbar\mathbf{p} \cdot \nabla V}{4m^2c^2} + \frac{\hbar\boldsymbol{\sigma} \cdot \mathbf{p} \times \nabla V}{4m^2c^2} \right] \xi(x) = E_s \xi(x)$$

Kinetic correction Darwin Spin-orbit

where ξ is a two-component spinor

spherical symmetry

$$-\frac{\mathbf{S} \cdot \mathbf{L}}{2m^2c^2} - \frac{1}{r} \frac{dV}{dr}$$

Since the spin-orbit coupling involves the gradient of the potential, the dominant contribution is near the nuclei

We assume that all SO is captured inside the PAW augmentation sphere where

$$|\psi_{n\sigma}\rangle = \sum_{ai} \langle \tilde{p}_i^a | \tilde{\psi}_n \rangle |\phi_i^a \sigma\rangle$$

The full SO Kohn-Sham Hamiltonian can then be set up in a basis of scalar-relativistic states

$$H_{n_1 n_2 \sigma_1 \sigma_2} = \delta_{\sigma_1 \sigma_2} \delta_{n_1 n_2} \epsilon_{n_1 \sigma_1} + \langle \psi_{n_1 \sigma_1} | H^{SO} | \psi_{n_2 \sigma_2} \rangle$$

$$\langle \psi_{n_1 \sigma_1} | H^{SO} | \psi_{n_2 \sigma_2} \rangle = \sum_{ai_1 i_2} \langle \tilde{\psi}_{n_1} | \tilde{p}_{i_1}^a \rangle \langle \phi_{i_1}^a \sigma_1 | H^{SO} | \phi_{i_2}^a \sigma_2 \rangle \langle \tilde{p}_{i_2}^a | \tilde{\psi}_{n_2} \rangle$$

For spherically symmetric potentials the atomic orbitals factorizes into a radial part and spherical harmonic

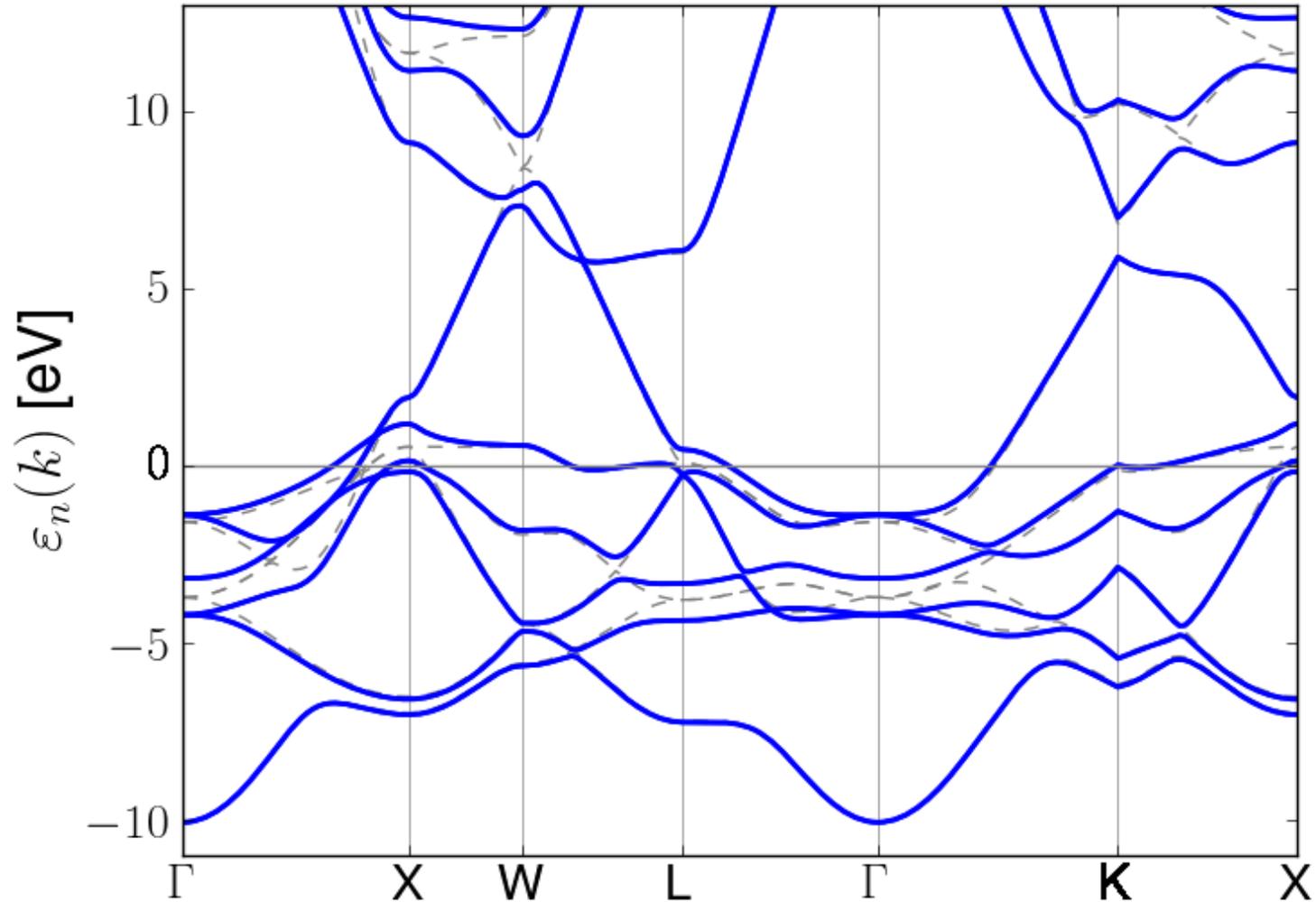
$$\phi_i^a(\mathbf{r}) = f_i(r)Y_i(\phi, \theta)$$

We thus have to evaluate

$$\begin{aligned} \langle \phi_{i_1}^a \sigma_1 | H^{SO} | \phi_{i_2}^a \sigma_2 \rangle &= \langle f_{i_1}^a Y_{i_1}^a \sigma_1 | H^{SO} | f_{i_2}^a Y_{i_2}^a \sigma_2 \rangle \\ &= -\frac{1}{2m^2 c^2} \langle Y_{i_1}^a \sigma_1 | \mathbf{S} \cdot \mathbf{L} | Y_{i_2}^a \sigma_2 \rangle \langle f_{i_1}^a | \frac{1}{r} \frac{dV}{dr} | f_{i_2}^a \rangle \end{aligned}$$

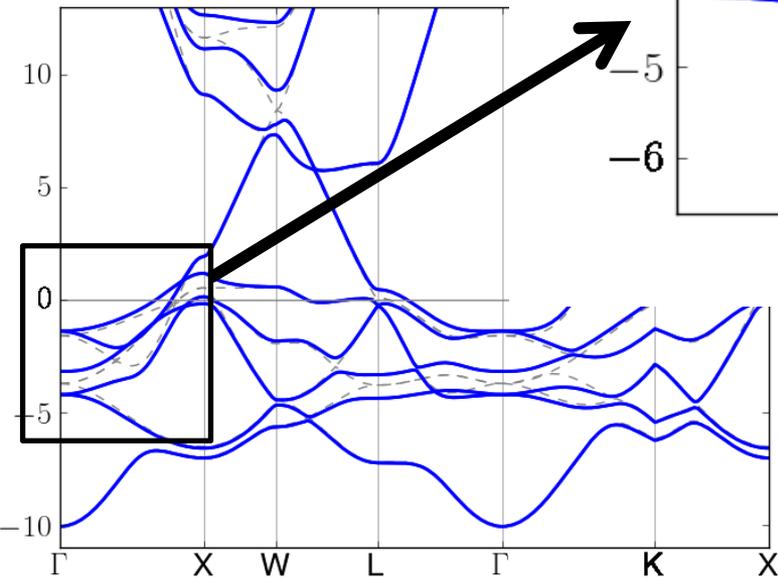
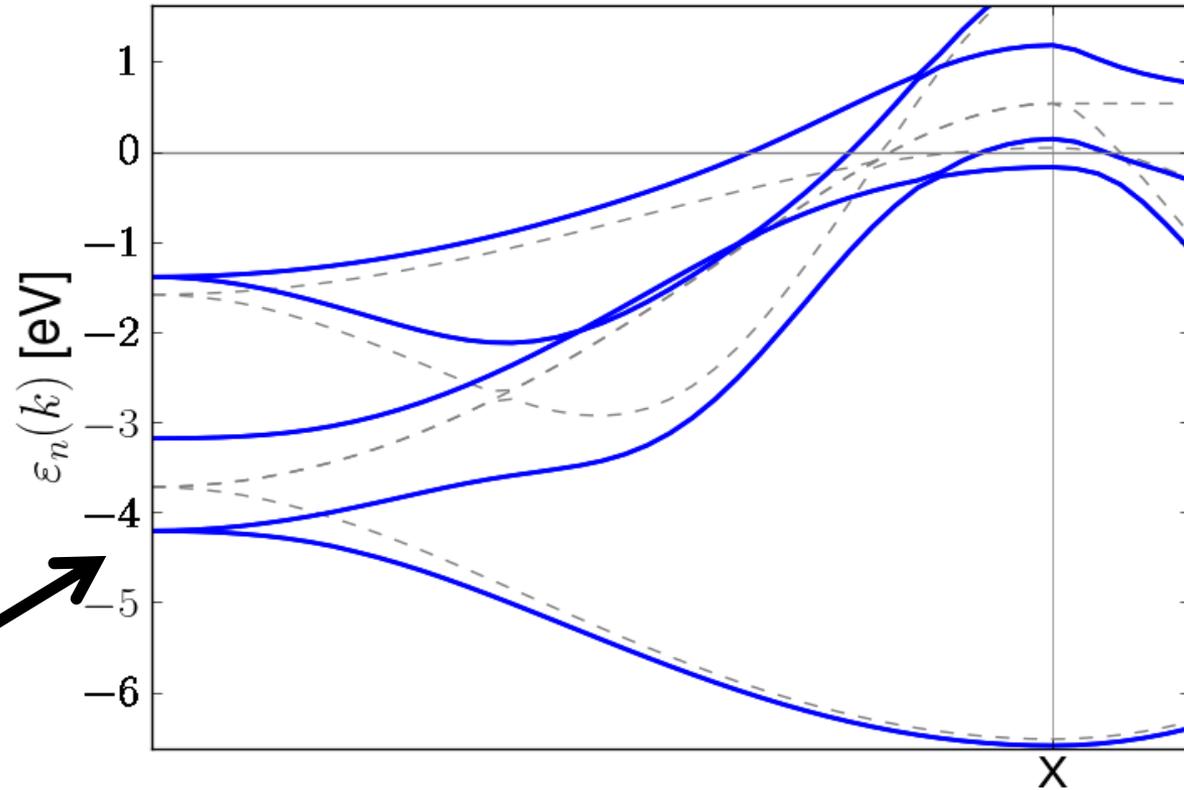
The radial part is calculated numerically on a non-uniform grid. The angular matrix elements have been tabulated. For example

$$\langle p_i | L_x | p_j \rangle = \begin{bmatrix} 0 & -i & 0 \\ i & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}, \quad i, j \in \{y, z, x\}$$



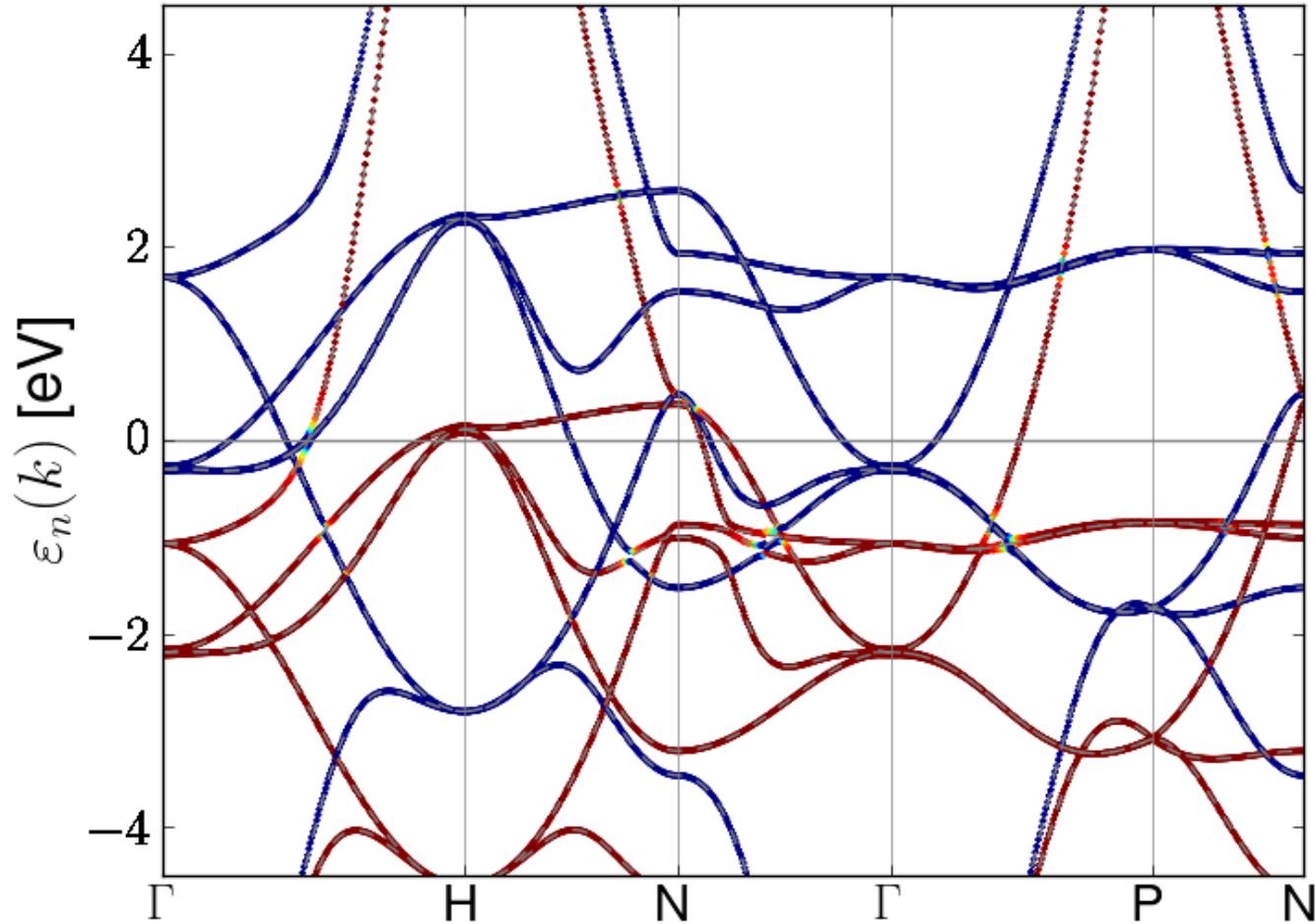
Spin degeneracy is protected by inversion symmetry

Spin-orbit corrections
of up to 1.5 eV



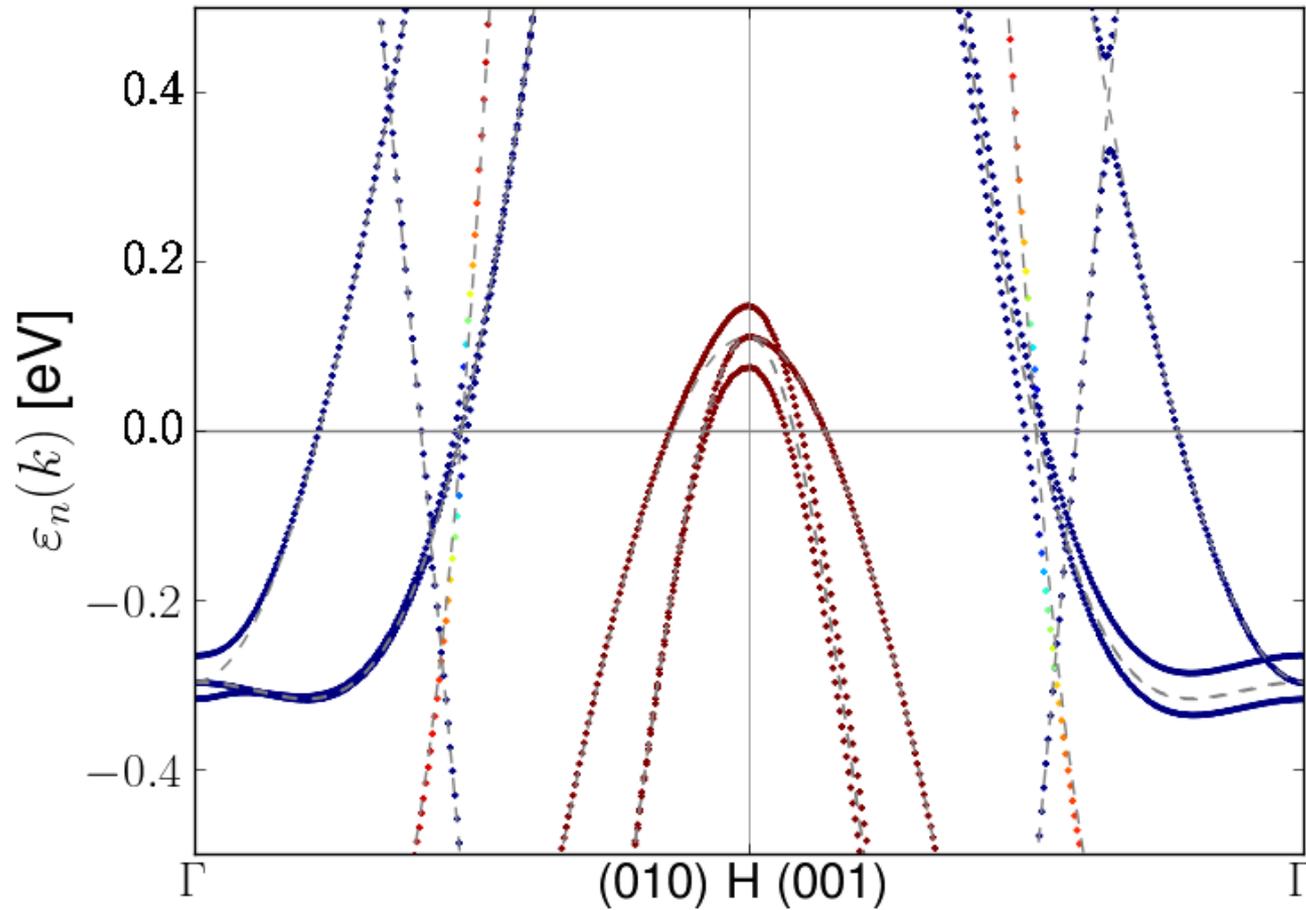
The double degenerate d states carry a two-dimensional irreducible representation of C_{4v}

Symmetry is reduced to C_4 by spin-orbit coupling



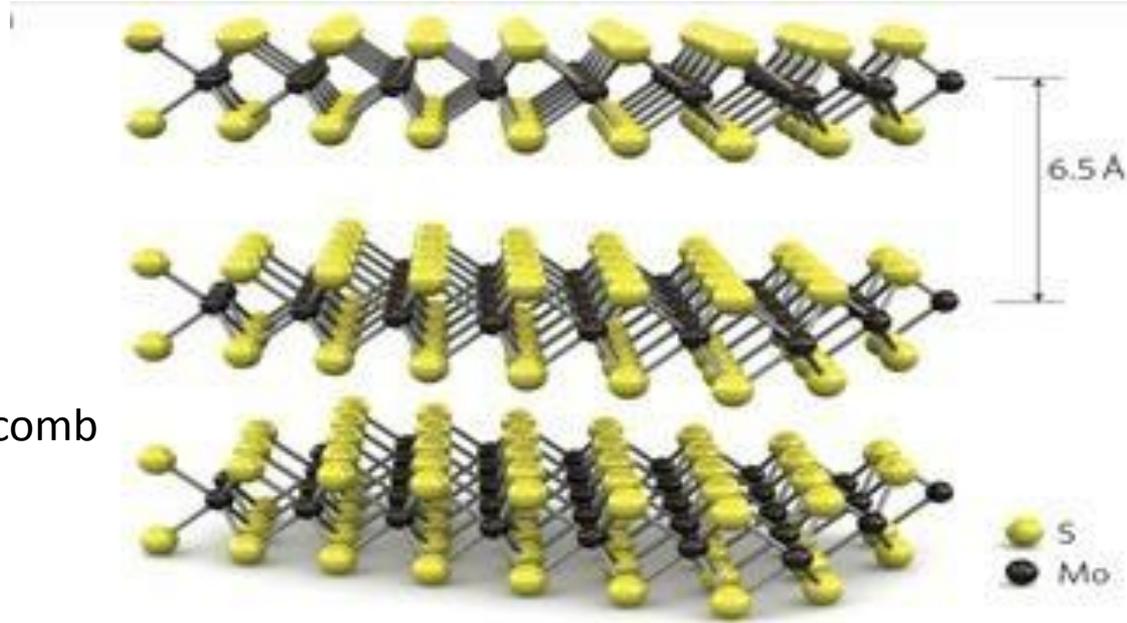
Color scale denotes spin character:

$$S_n(\mathbf{k}) = \langle \psi_{kn} | \sigma_z | \psi_{kn} \rangle$$

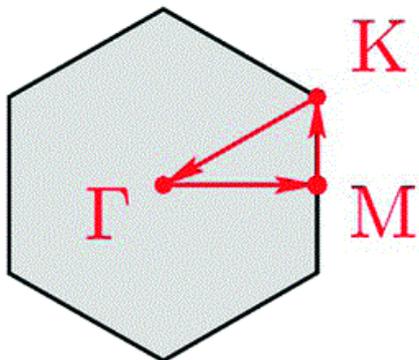
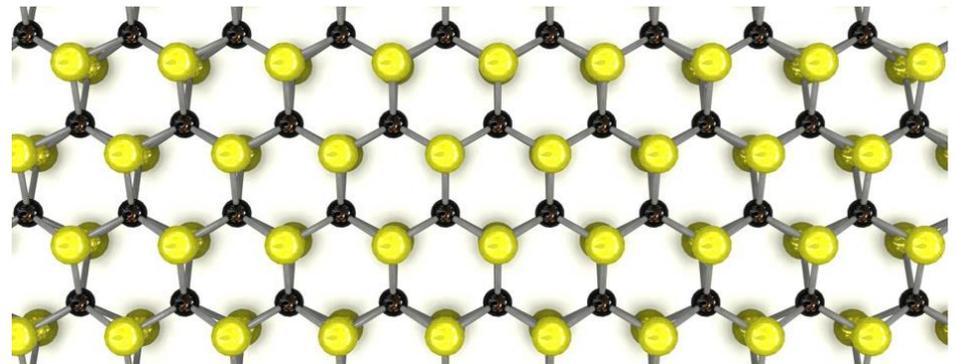


The band structure depends on the direction relative to the spin projection

Bulk MoS₂ is composed of stacked two-dimensional sheets bound by van der Waals interactions

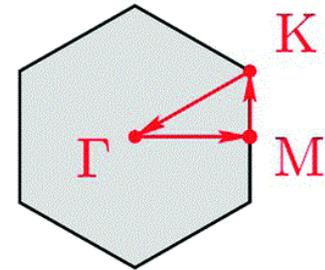
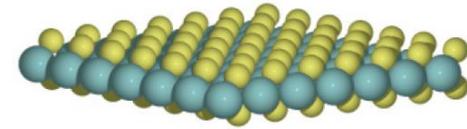
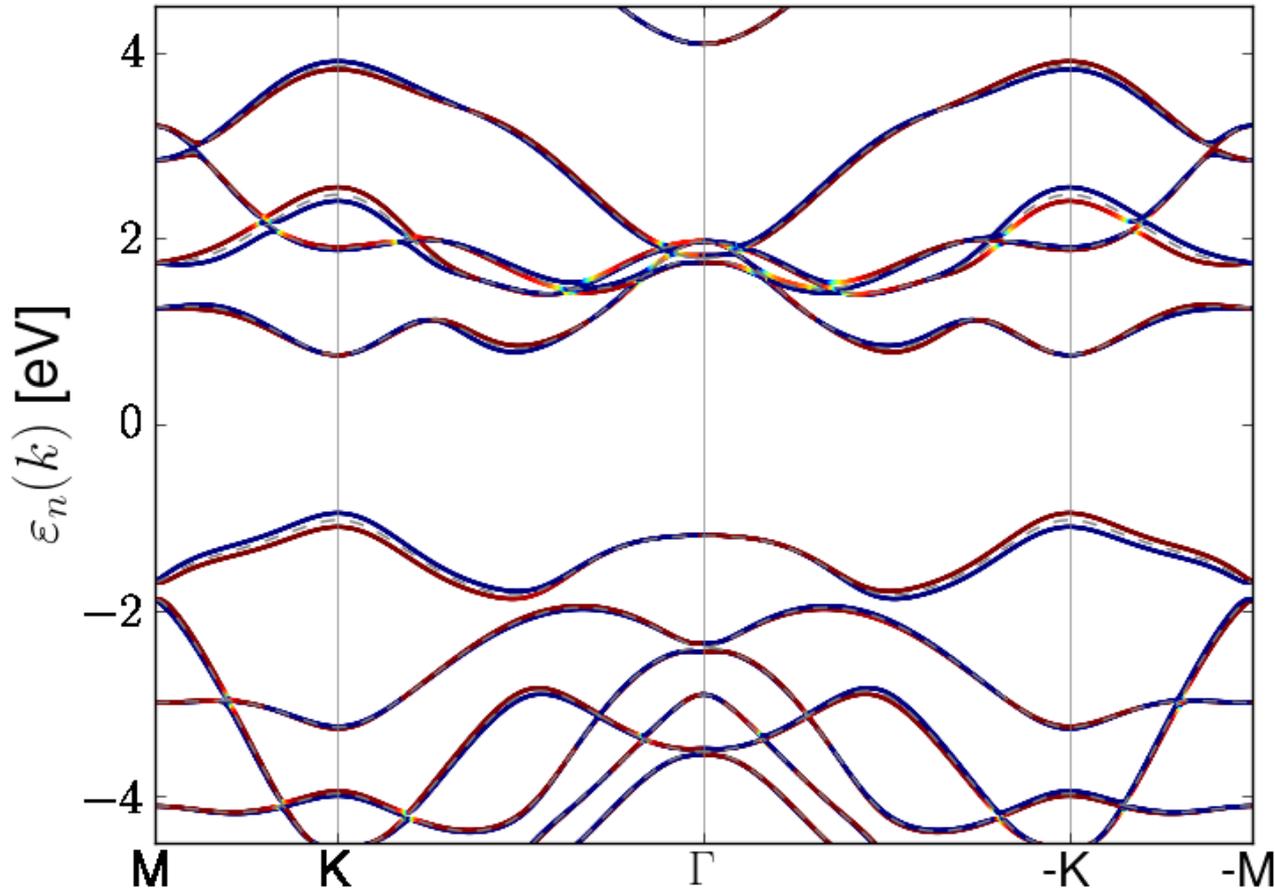


The individual sheets have a honeycomb lattice similar to graphene or hBN



Brillouin zone

Lack of inversion symmetry



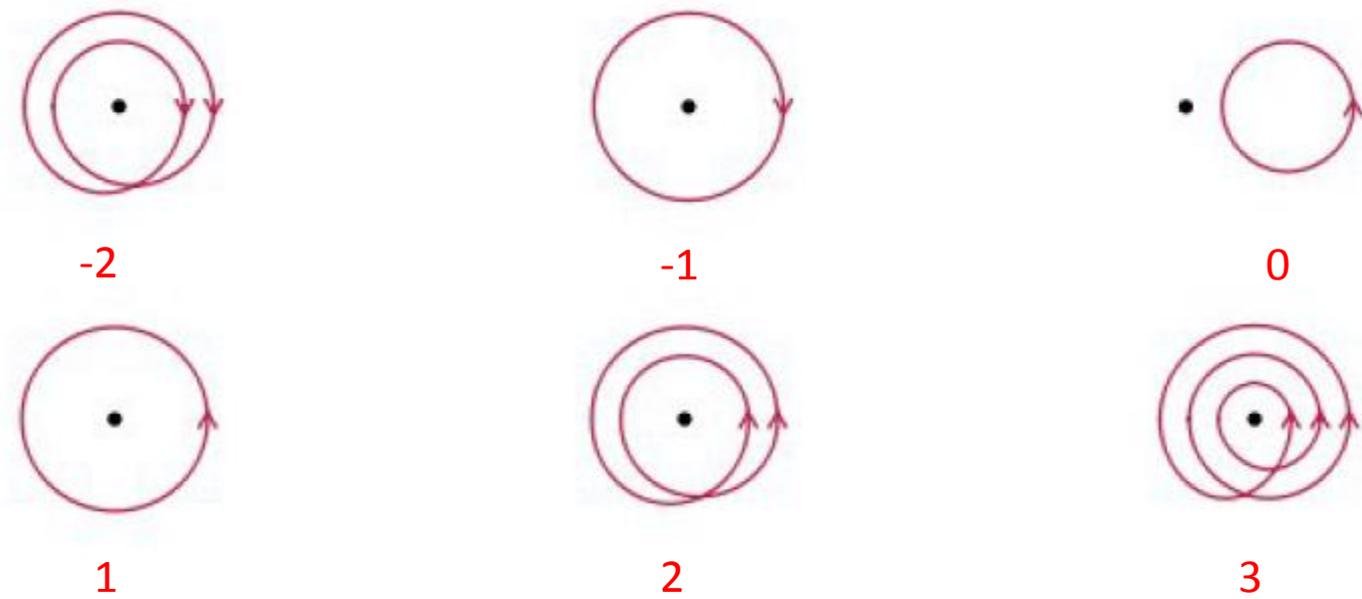
$\delta = 0.149 \text{ eV}$

Color scale denotes spin character:

$$S_n(\mathbf{k}) = \langle \psi_{kn} | \sigma_z | \psi_{kn} \rangle$$

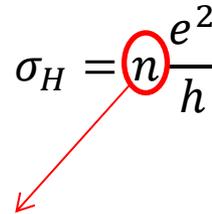


Number of holes in two-dimensional manifolds



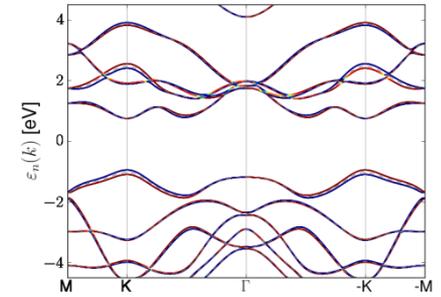
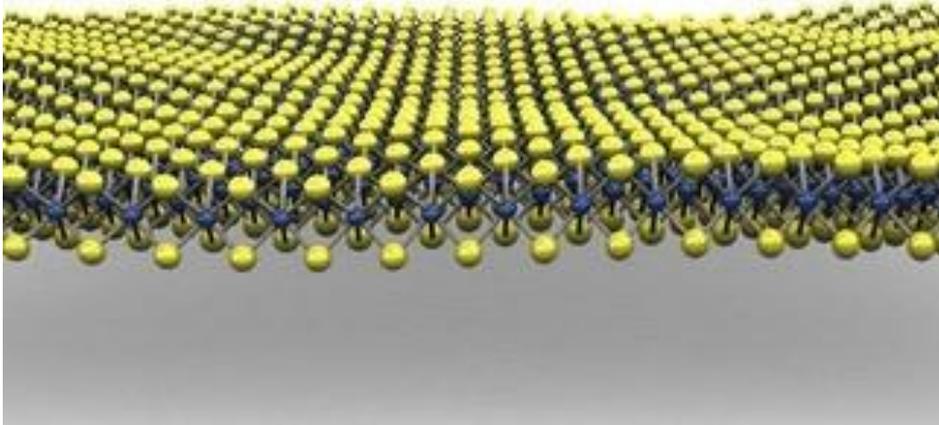
Winding number around "stick"

Quantum Hall conductivity: $\sigma_H = n \frac{e^2}{h}$

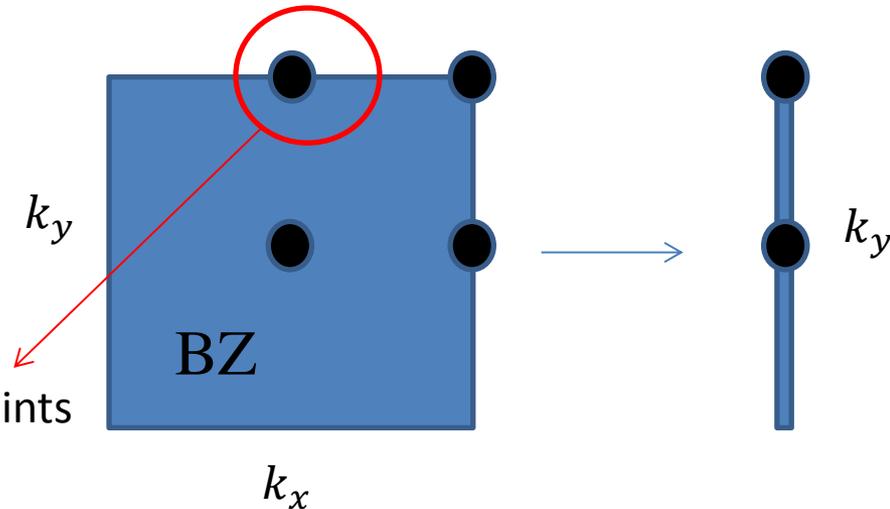


Winding number of occupied Bloch states around Brillouin zone edge

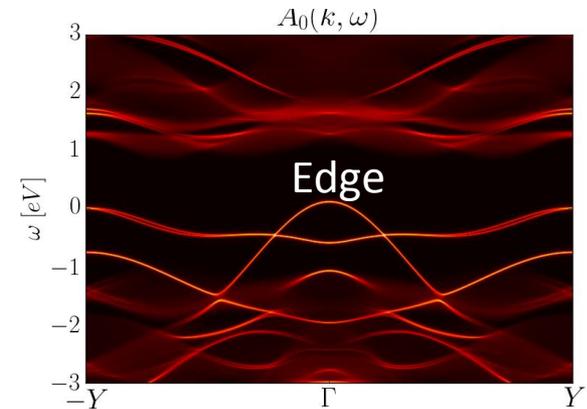
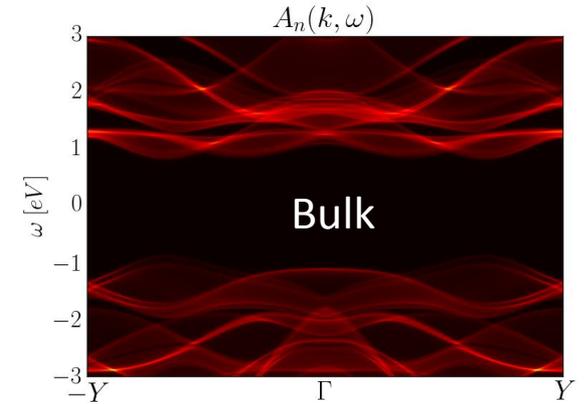
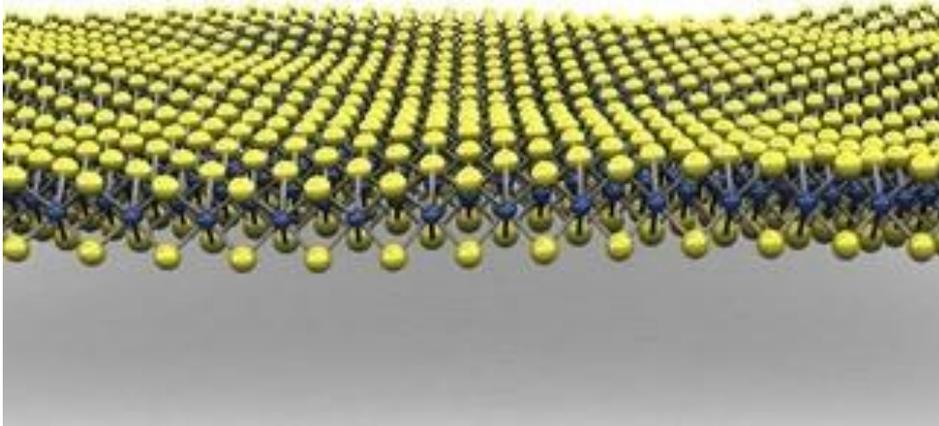
Edges of two-dimensional insulator



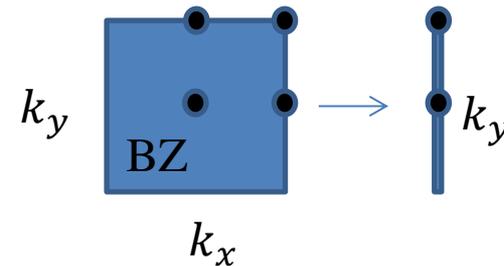
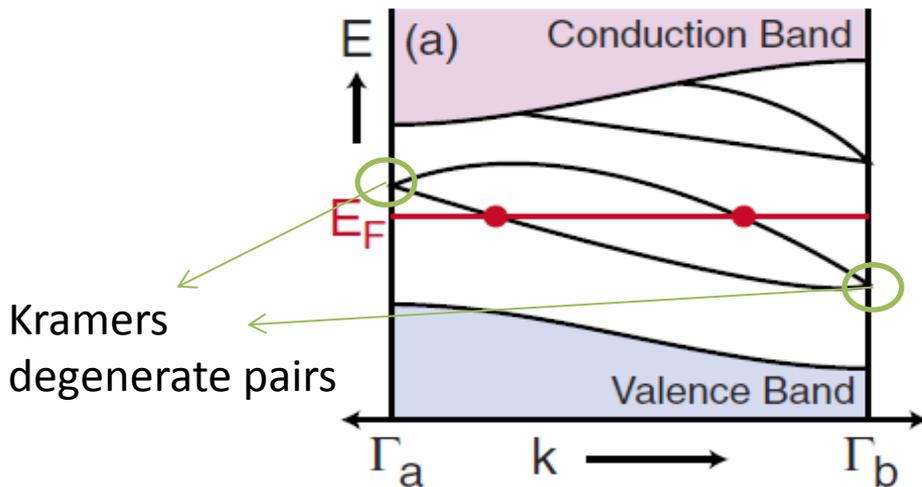
Bulk 2H-MoS₂

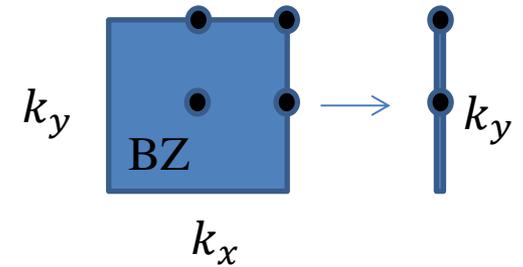
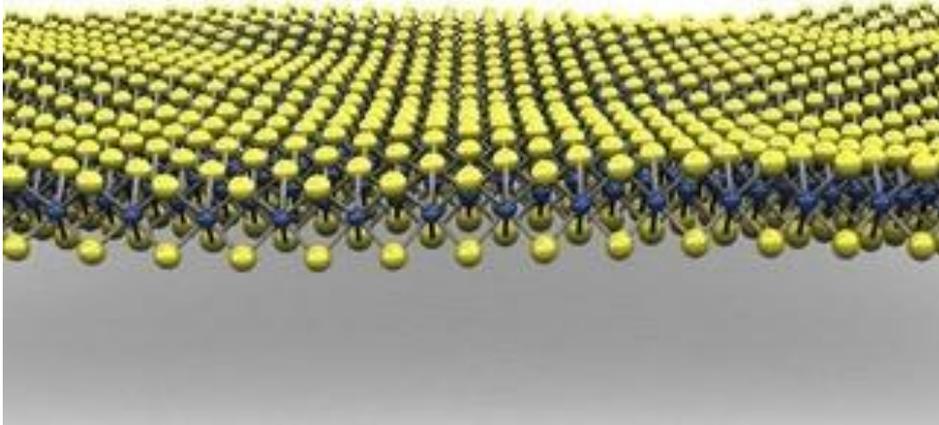


Time-reversal invariant points

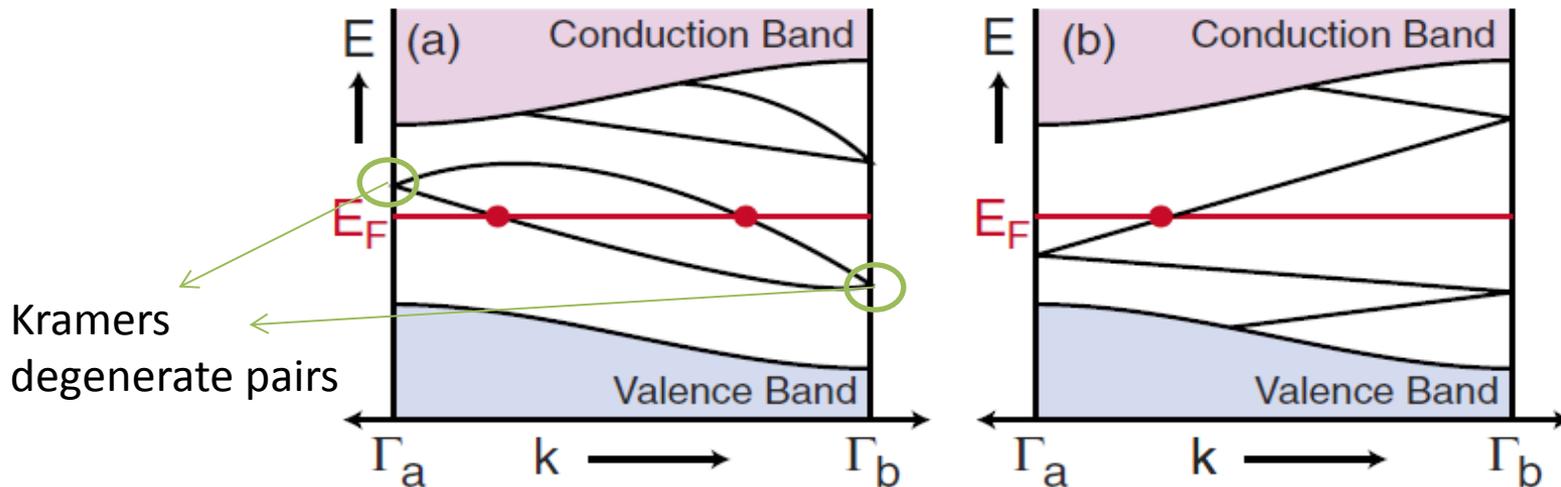


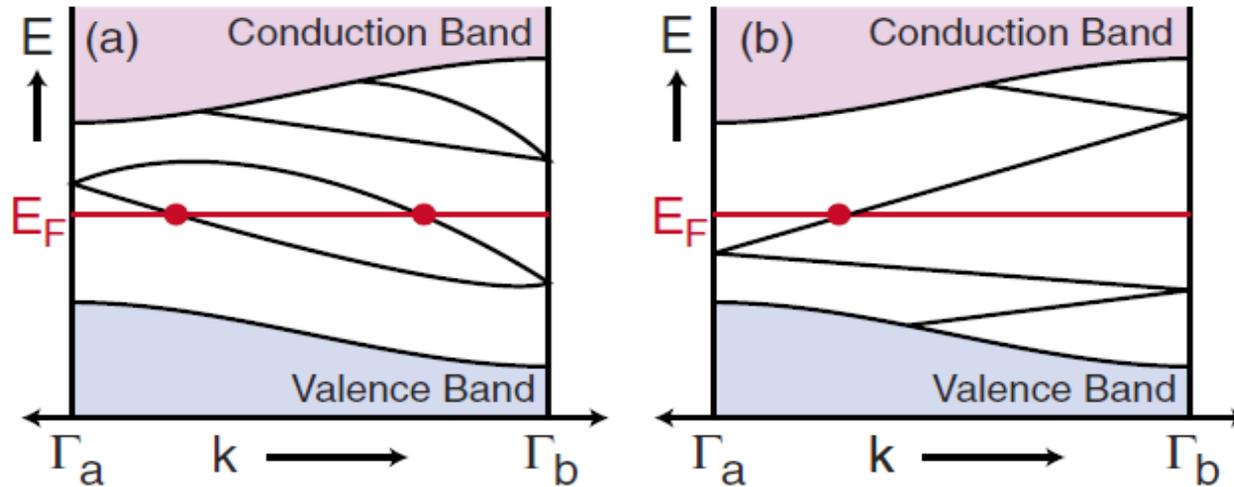
Two things may happen at the edge:



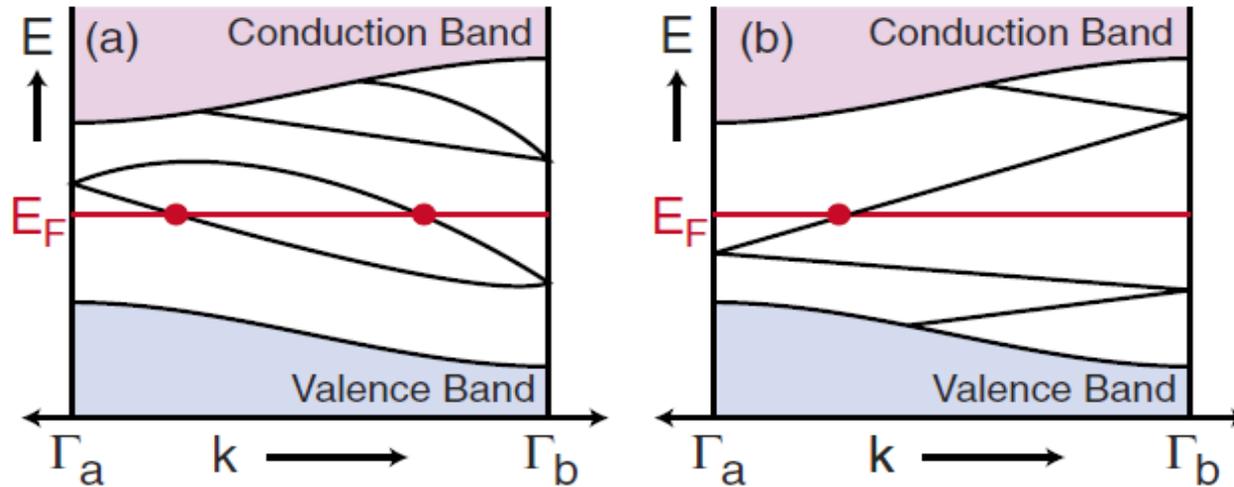


Or:





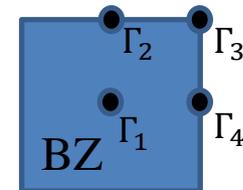
The distinction between odd or even number of crossings at edges is a property of the bulk material and comprises a topological Z_2 classification of 2D insulators



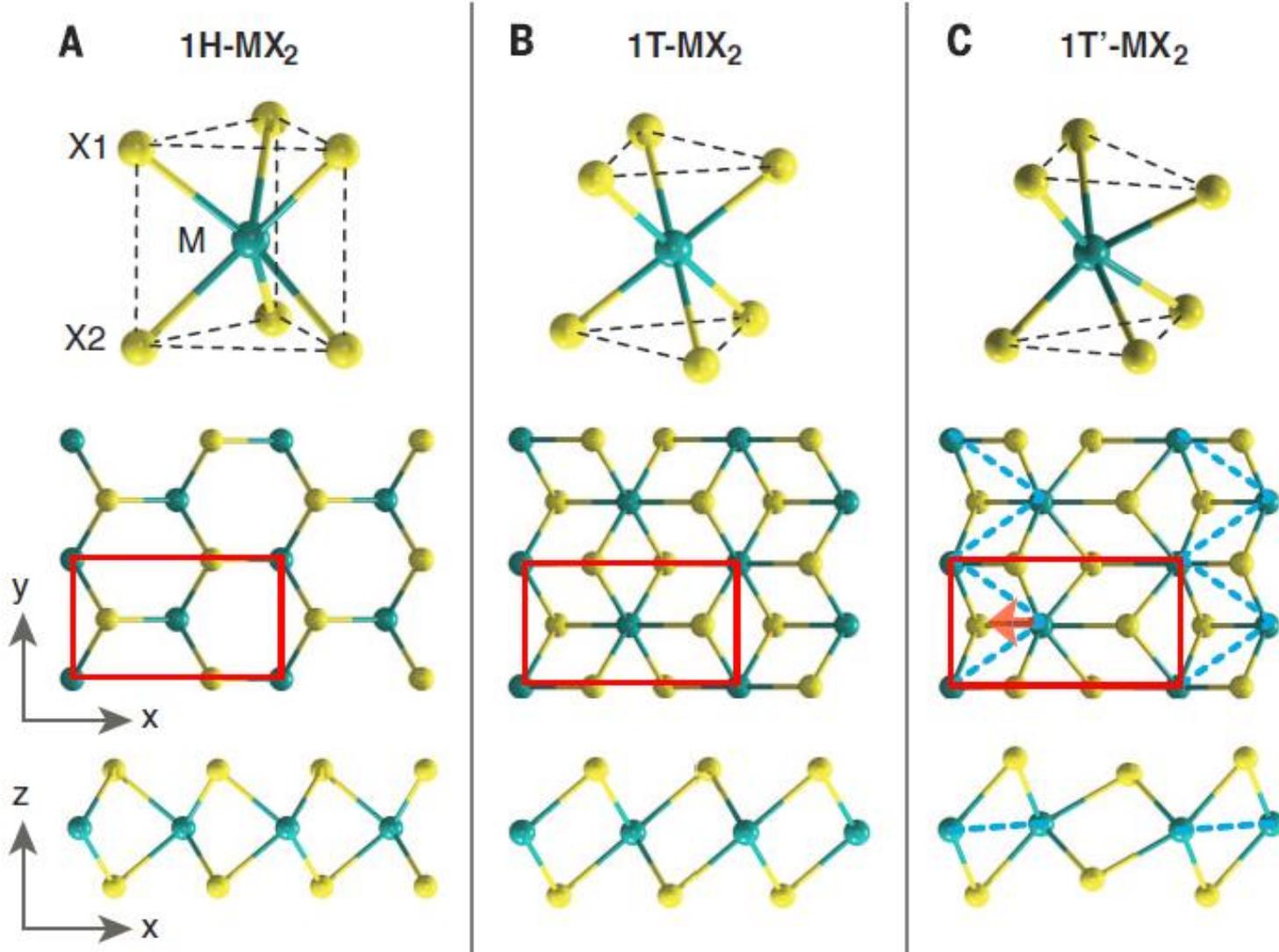
The distinction between odd or even number of crossings at edges is a property of the bulk material and comprises a topological Z_2 classification of 2D insulators

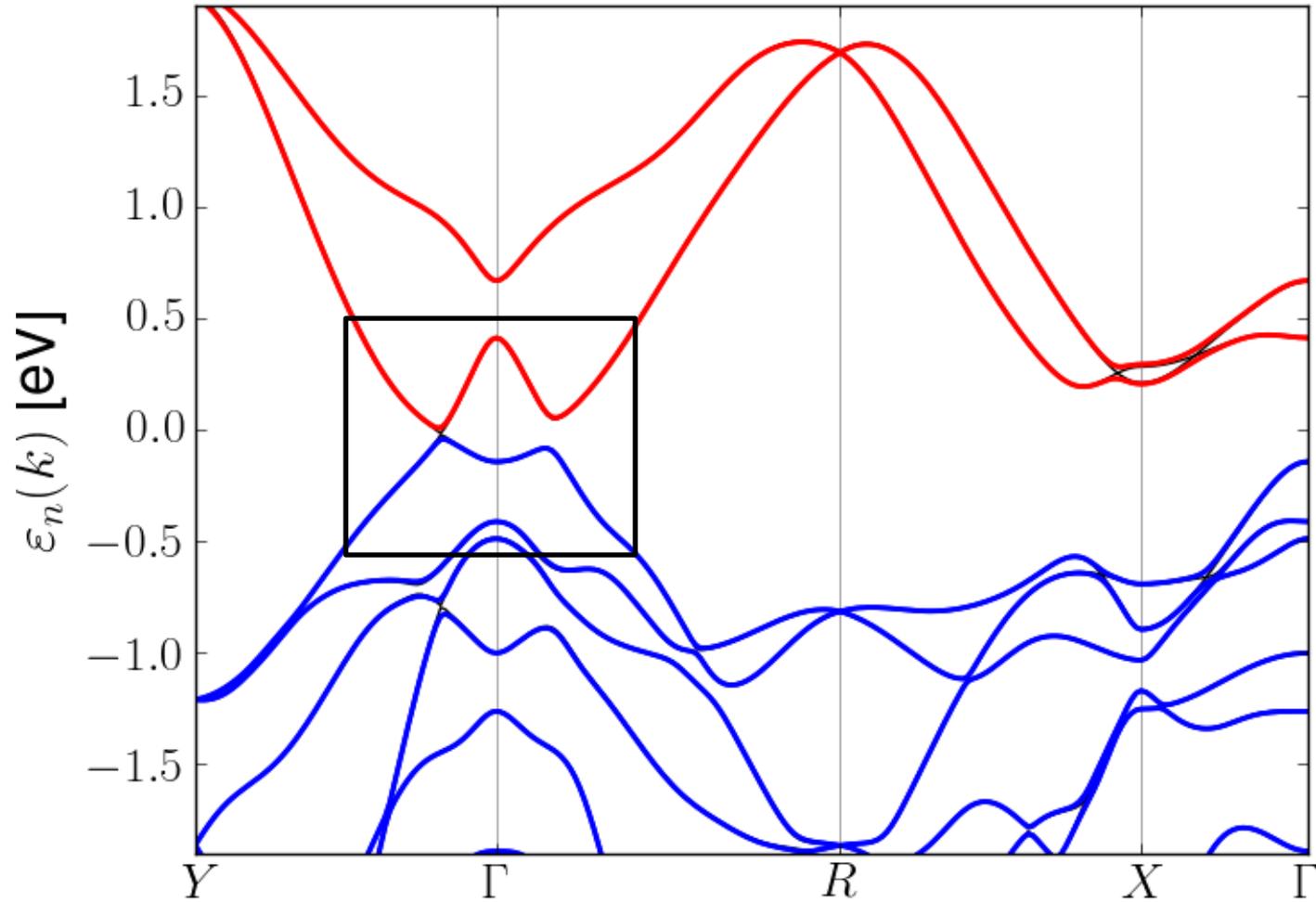
For materials with inversion symmetry the topological index ν can be calculated as

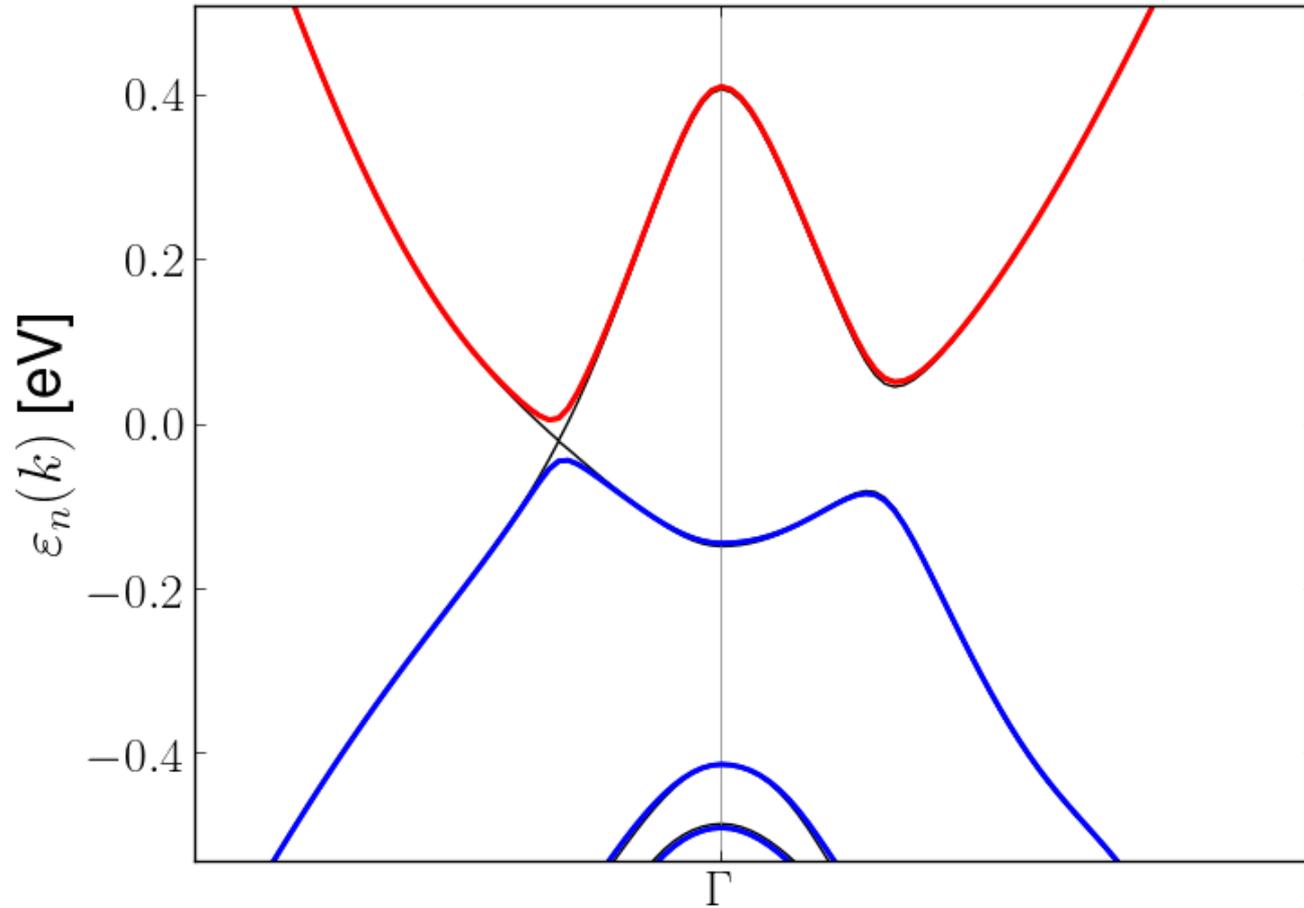
$$(-1)^\nu = \prod_{\Gamma_a} \prod_m \xi_m(\Gamma_a)$$



Where the product is over occupied Kramers pairs of inversion eigenvalues at the TR invariant points – implemented in GPAW in pw mode







$$\prod_{\Gamma_a m} \xi_m(\Gamma_a) = -1$$

Edge states can be obtained by calculating the spectral function in a local basis set:

$$A_S(k_{\parallel}, \omega) = -\frac{1}{\pi} \sum_{i \in S} \text{Im} G_{ii}^R(k_{\parallel}, \omega)$$

$$G_{ij}^R = (\omega + i\eta - H_{ij})^{-1}$$



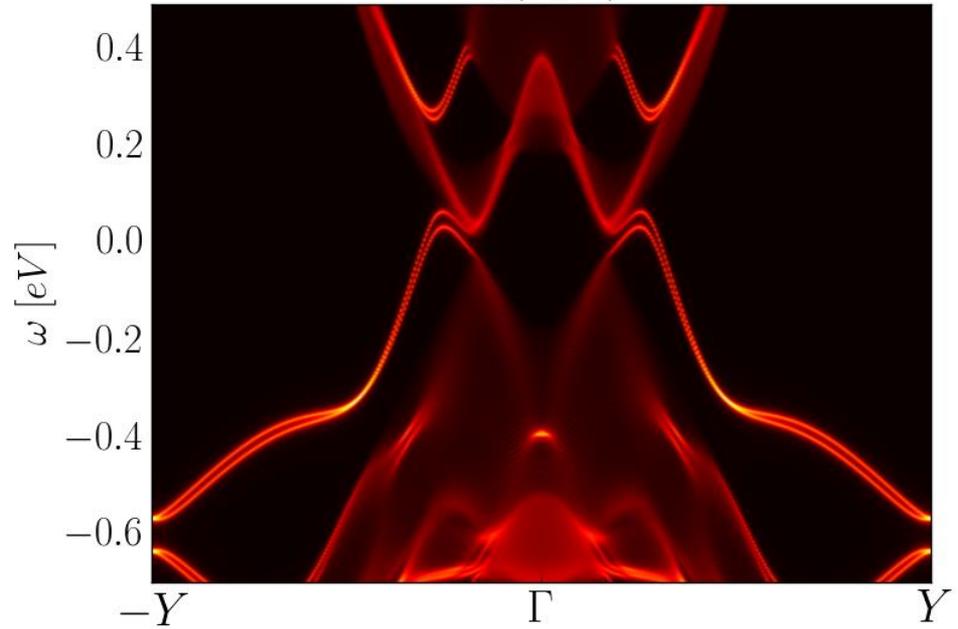
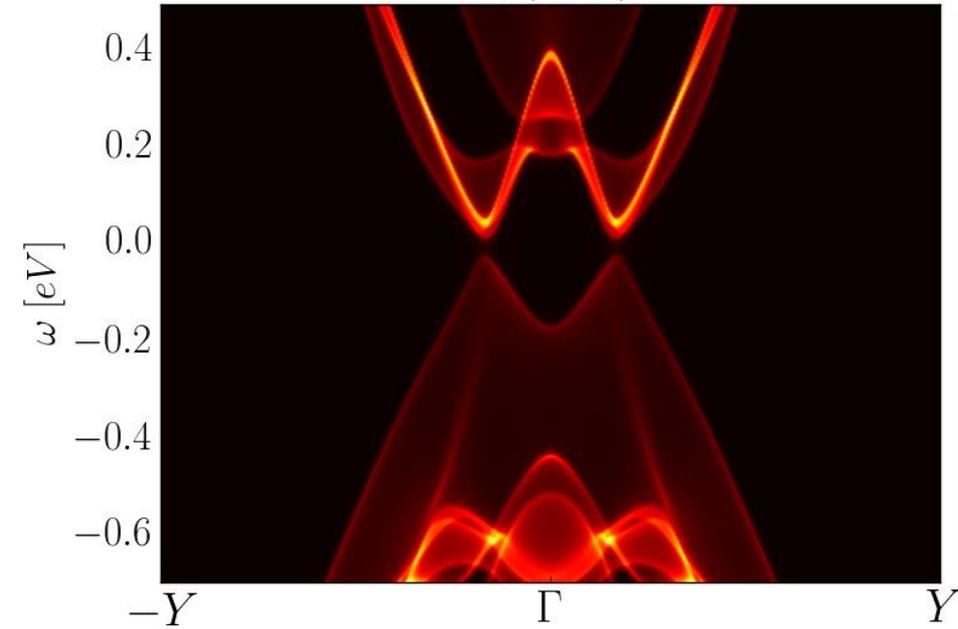
The Greens functions can be obtained iteratively once the Hamiltonian is transformed to a local basis

Sancho et al. *J. Phys. F* **15**, 851 (1985)

The transformation is accomplished with Wannier functions using Wannier90. Interface recently been implemented in GPAW – see tutorial for details

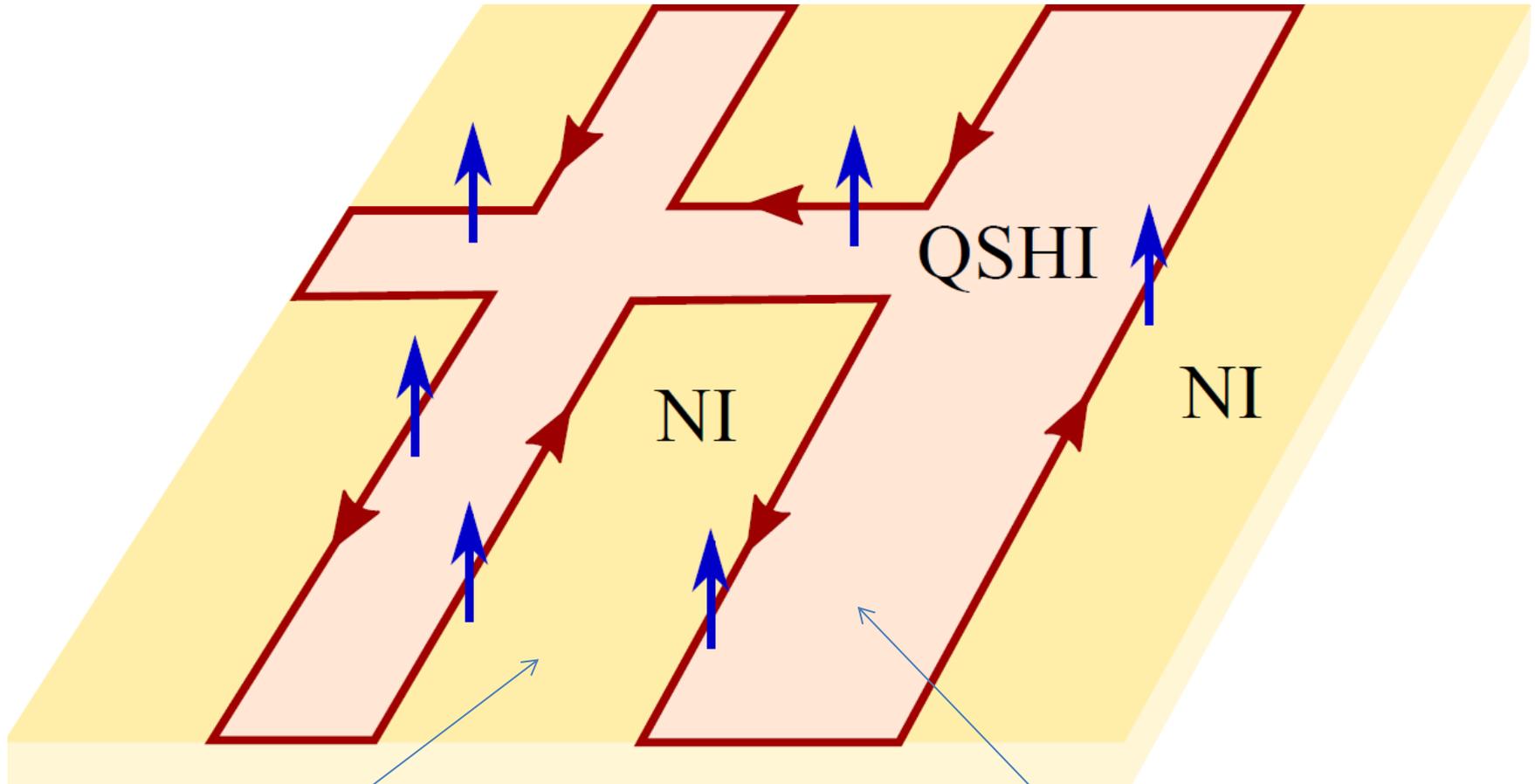
$$A_n(k, \omega)$$

$$A_0(k, \omega)$$



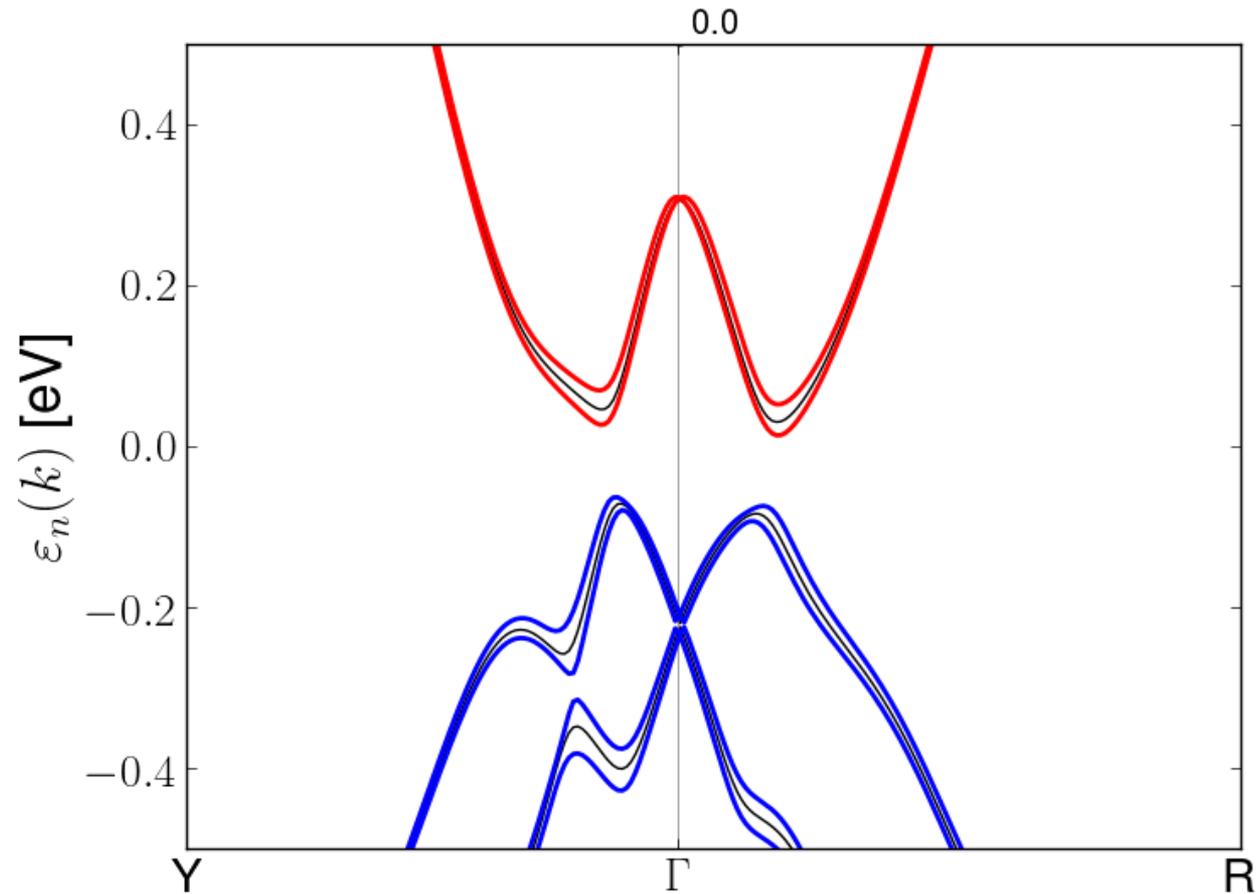
Bulk spectral function

Surface spectral function

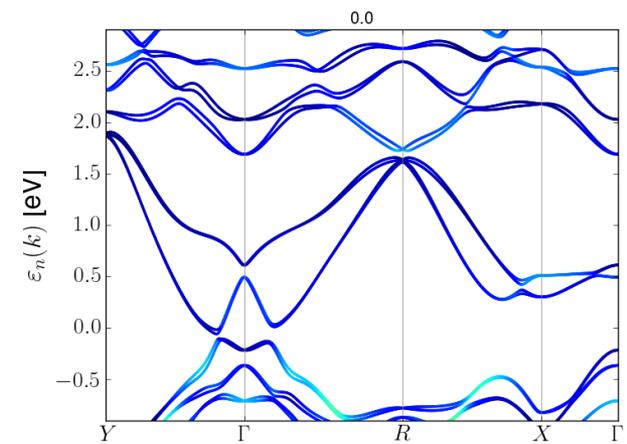
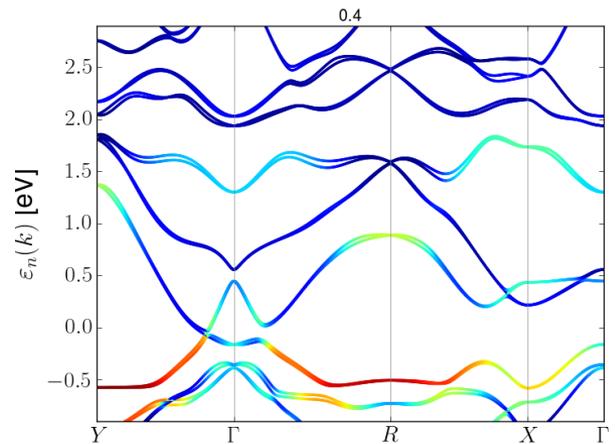
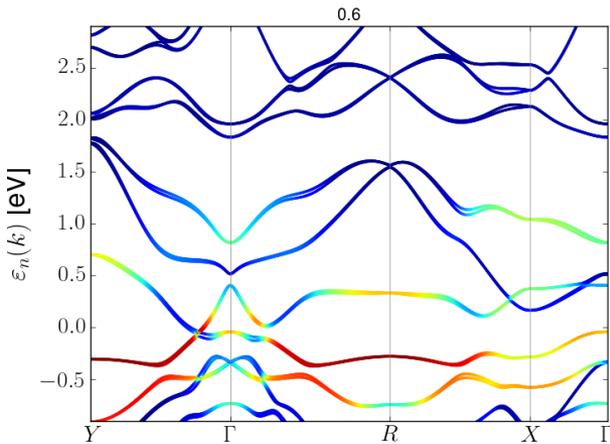
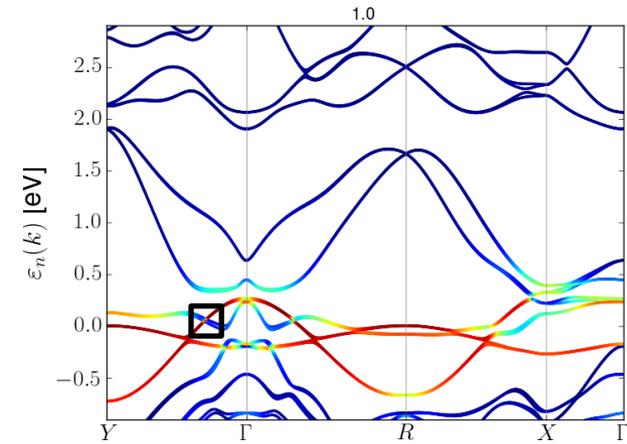
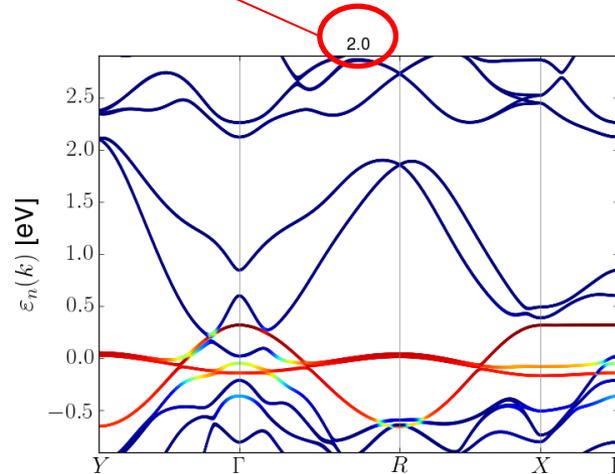
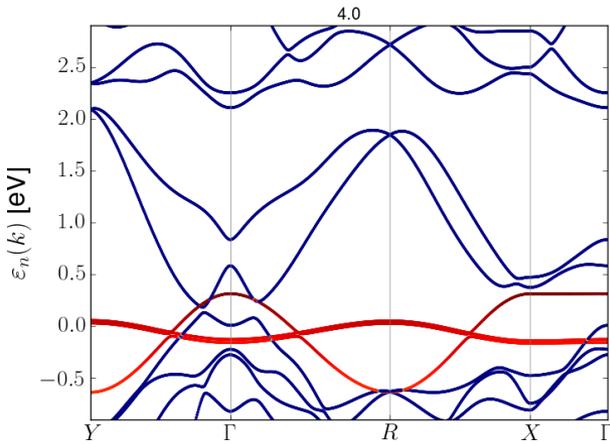


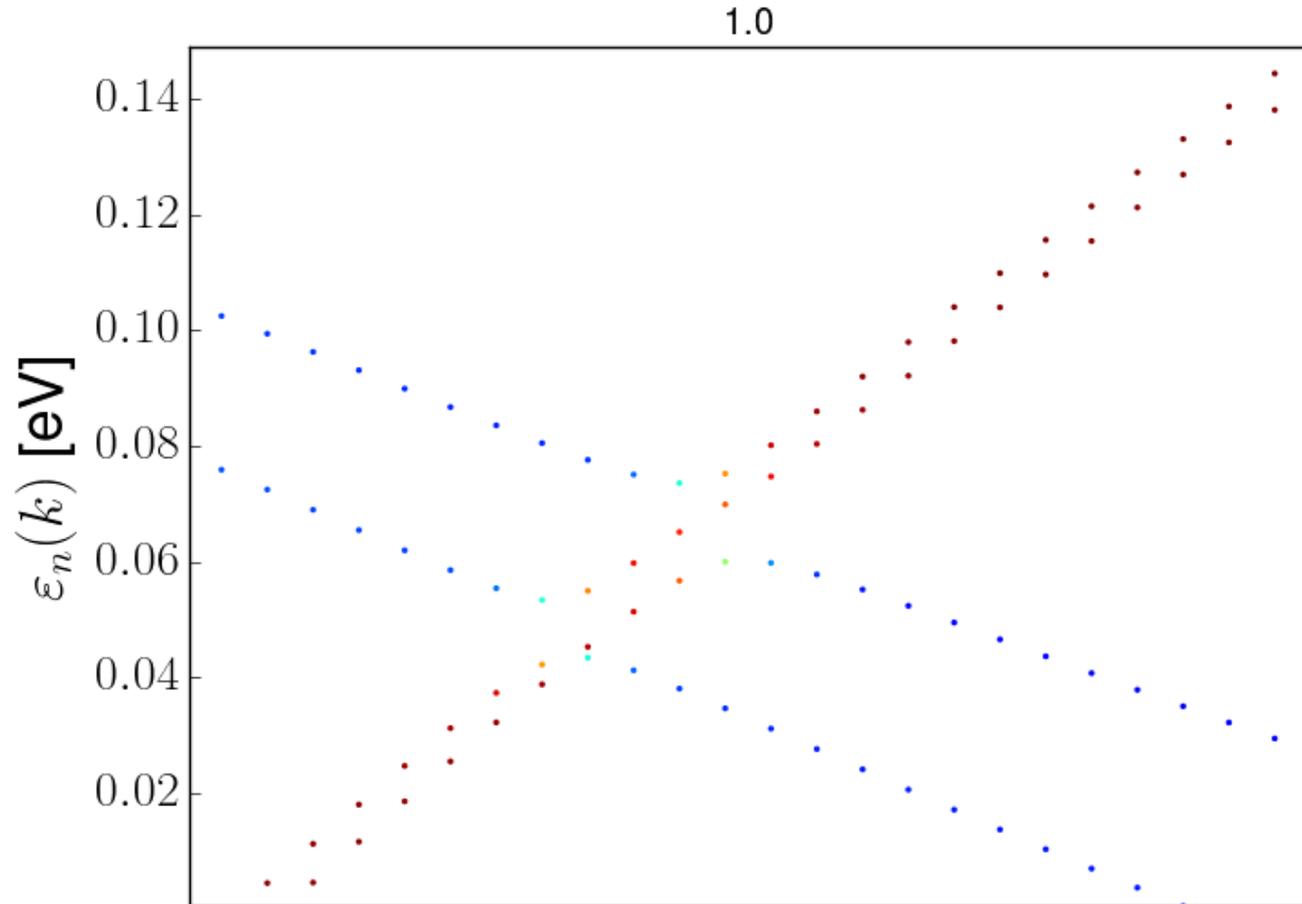
Normal Insulator

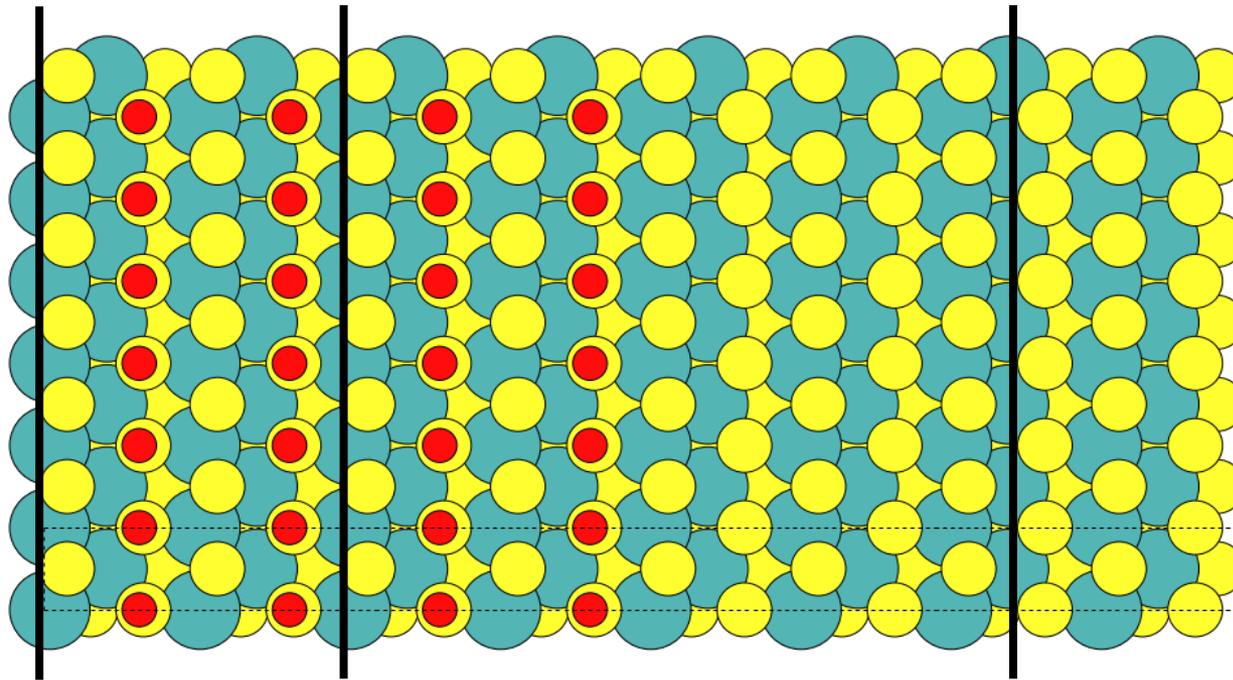
Topological Insulator
(Quantum Spin Hall Insulator)



Distance from equilibrium

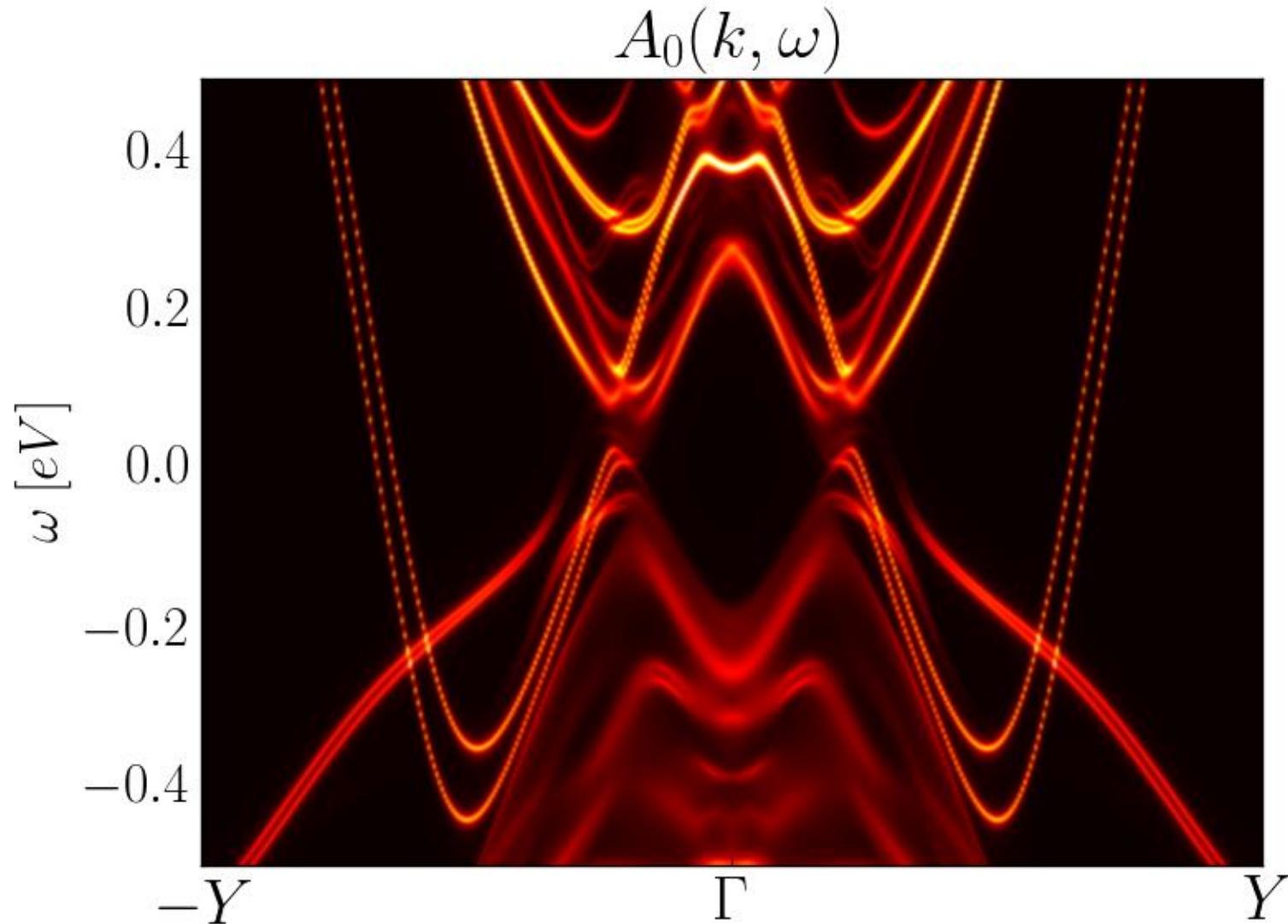


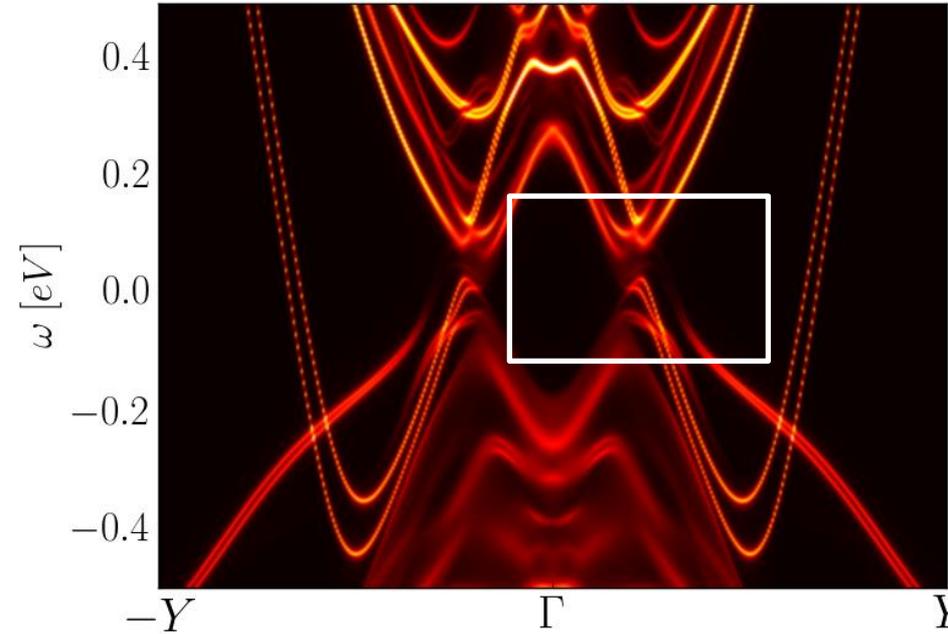




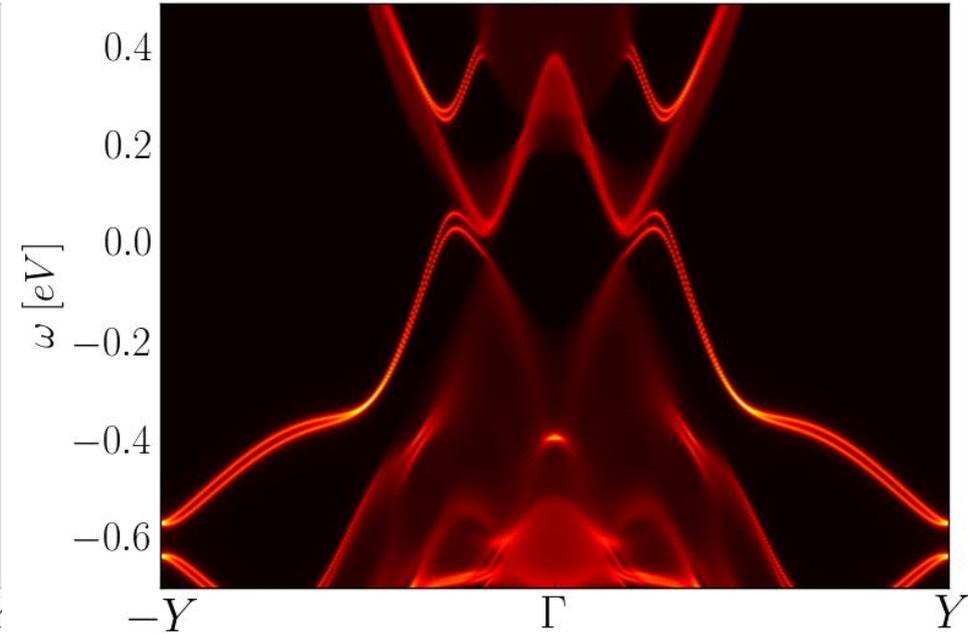
$$\begin{array}{cccccccc}
 \dots H_{11} & H_{11} & & H_{22} & & H_{33} & H_{33} \dots & \\
 \dots H_{01} & H_{01} & H_{12} & & & H_{23} & H_{34} & H_{34} \dots
 \end{array}$$

Retarded Greens function at interface can be obtained iteratively



$A_0(k, \omega)$ 

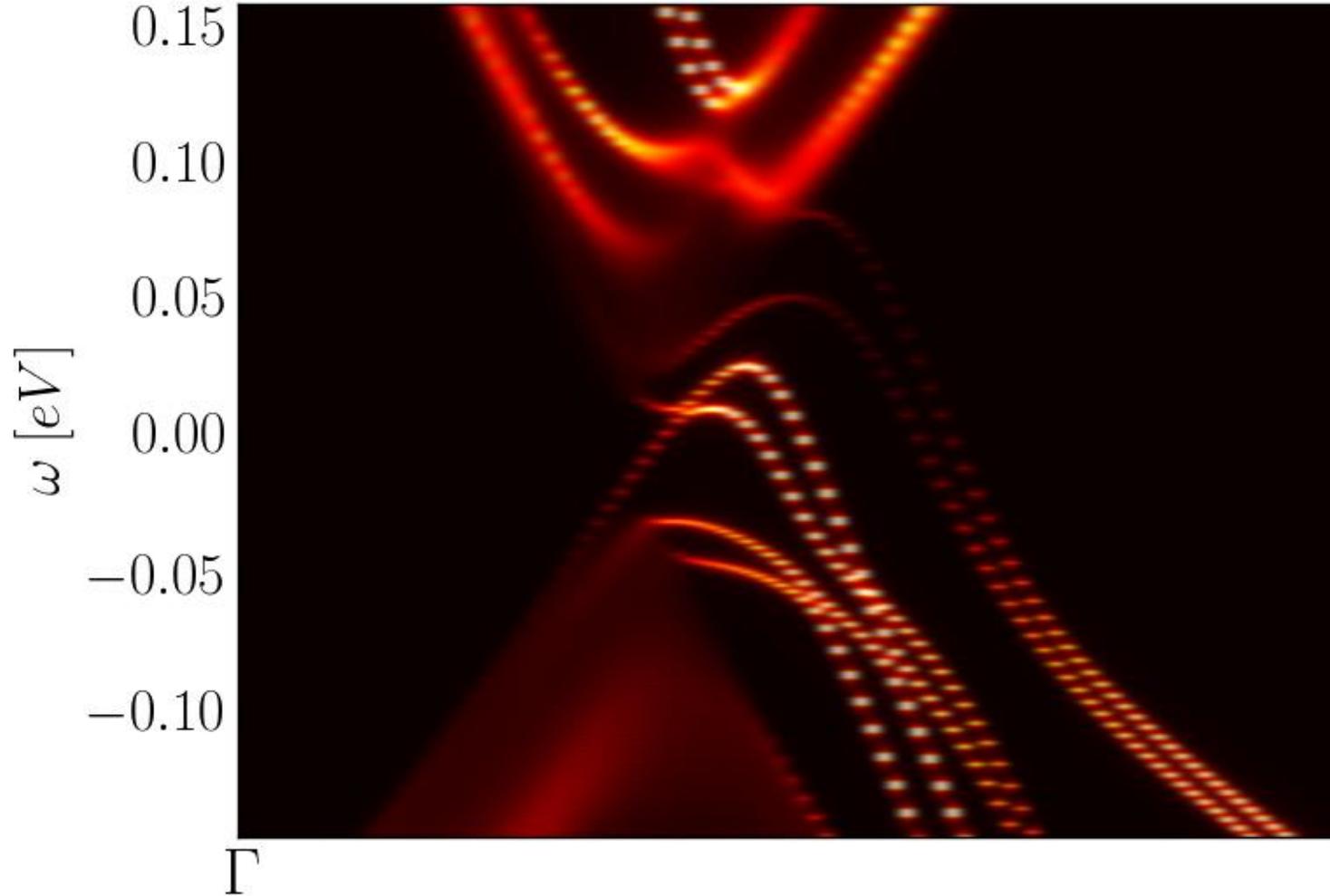
Interface with oxygen adsorbate region

 $A_0(k, \omega)$ 

Bare edge

1T'-MoS₂ – partly adsorbed O

$$A_0(k, \omega)$$



Outlook

- Topological in-plane heterostructures could comprise a clever way of designing 1D electronics
- Many other adsorbates are possible
- The topological boundary states needs to be analyzed further. What about other edges?
- The structure is hardly thermodynamically stable!

Thank you for the attention